

# HSM112WK

## Silicon Schottky Barrier Diode for Battery Switch

# HITACHI

Preliminary  
Rev.2  
Feb. 1993

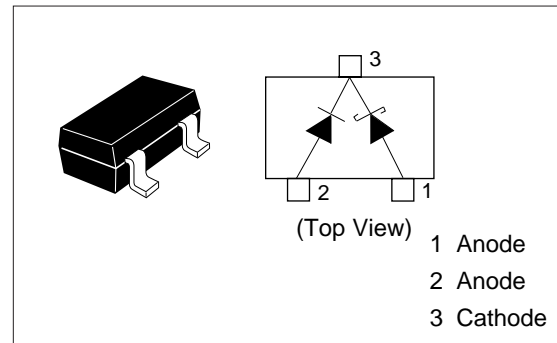
### Features

- The HSM112WK has two different ( $V_F$ -  $I_F$ ) chips, and can change the main battery to the backup battery automatically.
- MPAK package is suitable for high density surface mounting and high speed assembly.

### Ordering Information

Type No.	Laser Mark	Package Code
HSM112WK	S 2	MPAK

### Pin Arrangement

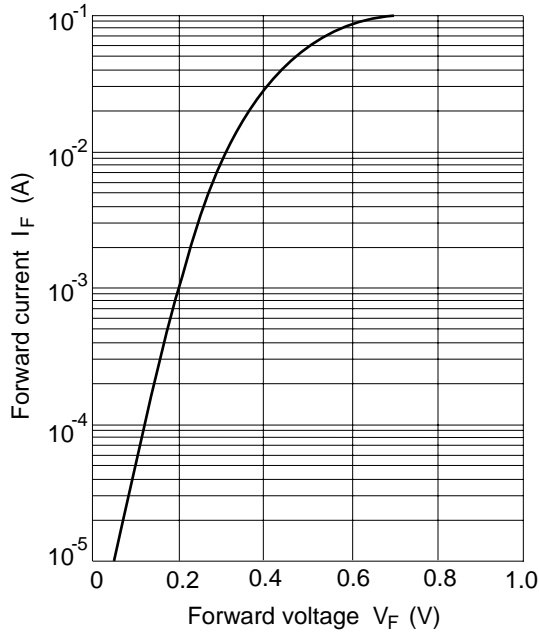


### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

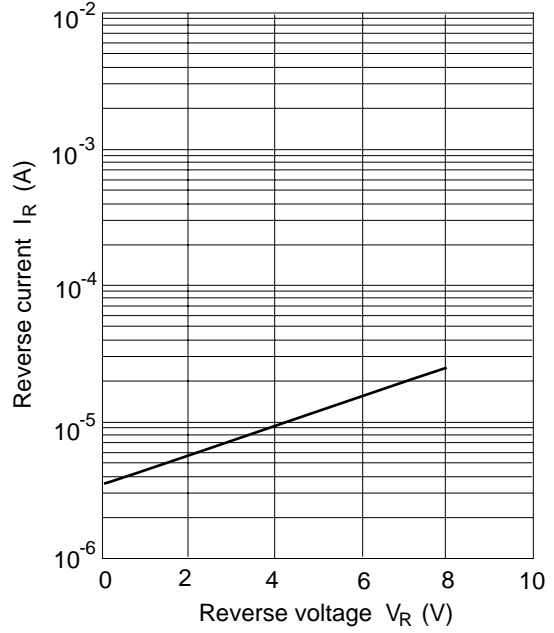
Item	Symbol	Value Pin 1-3	Value Pin 2-3	Unit
Peak reverse voltage	$V_{RM}$	8	10	V
Forward current	$I_F$	30	30	mA
Junction temperature	$T_j$	125	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +125	-55 to +125	$^\circ\text{C}$

### Electrical Characteristics ( $T_a = 25^\circ\text{C}$ )

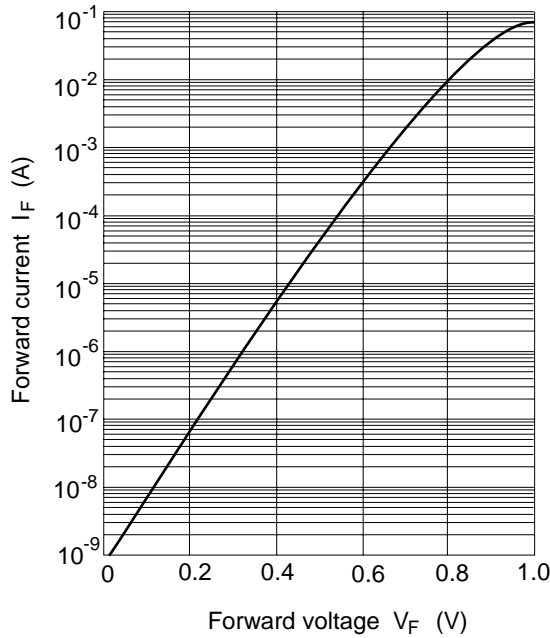
Item	Symbol	Min	Typ	Max	Unit	Test Condition	
Forward voltage	$V_F$	Pin 1-3	0.1	—	0.3	V	$I_F = 1 \text{ mA}$
		Pin 2-3	0.5	—	0.8		
Reverse current	$I_R$	Pin 1-3	—	—	30	$\mu\text{A}$	$V_R = 5 \text{ V}$
		Pin 2-3	—	—	0.1		



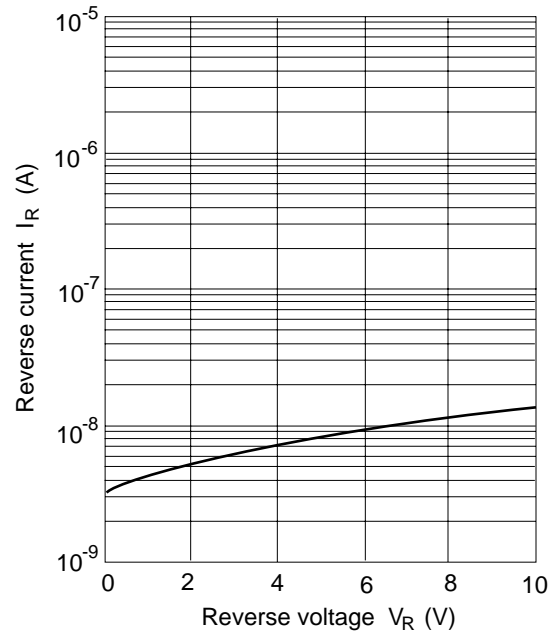
**Fig.1 Forward current Vs. Forward voltage (Pin1-3)**



**Fig.2 Reverse current Vs. Reverse voltage (Pin1-3)**



**Fig.3 Forward current Vs. Forward voltage (Pin2-3)**



**Fig.4 Reverse current Vs. Reverse voltage (Pin2-3)**

Package Dimensions

Unit: mm

